DEVELOPMENT OF A HIGHLY EFFICIENT ENERGY KICKER FOR LONGITUDINAL BUNCH-BY-BUNCH FEEDBACK

M. Masaki, T. Fujita, K. Kobayashi, T. Nakamura, M. Oishi, H. Ohkuma, S. Sasaki, M. Shoji



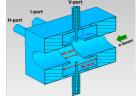
Japan Synchrotron Radiation Research Institute (JASRI/SPring-8)

Highly Efficient New Energy Kicker

Originally Designed and Developed Kicker in SPring-8 High Kick Efficiency per Length

Three Times Higher than Conventional WOC type





Longitudinal Kicker

Inner Structure of One Cell

3-cell Structure

Three Kicker Cells are embedded in the vacuum chamber.

Kicker Cell

Cavity Length 96 mm, Electrode Gap 40 mm

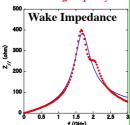
Driving RF Frequency

 $(3+1/4) f_{RF} = 1.65 GHz$ RF reference frequency $f_{RF} = 508.58 \text{ MHz}$

Beam is kicked by a Single Resonant Mode excited at the driving frequency.

The resonant mode is required to have low Q-factor, i.e. fast damping time of several nanoseconds.

Longitudinal Wake Impedance (Calculation) Assuming bunch length of 6mm (r.m.s.) Estimated Q-factor by Lorentzian fitting $Q \sim 4.2$



Driving RF Power

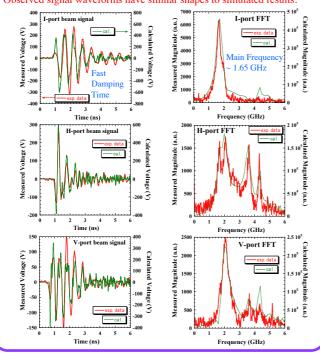
Input from symmetrically attached two I-ports at the same timing **Removal of Unwanted Higher Order Modes**

Removed from two pairs of ports (H-ports, V-ports) attached symmetrically.

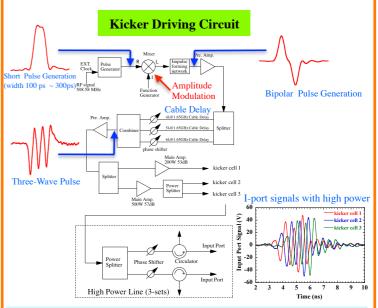
Kicker body made of Copper with high thermal conductivity Water-cooled copper body and high power feed-through ports (I-port)

Response to a Single Bunch Beam

Beam signals observed at each port (I-port, H-port and V-port) Observed signal waveforms have similar shapes to simulated results.



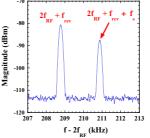
Beam Kick Test & Kick Performance

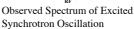


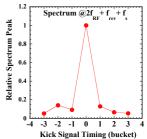
Electron bunches are kicked by using resonance of the synchrotron oscillation. Kick voltage was amplitude-modulated with $f_{rov} + f_s$.

Bunch Fill Pattern: 84 bunches equal spacing (57 ns interval)

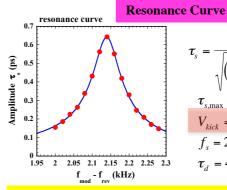
Mod. Freq.: f_{rev} (208.8 kHz @Revolution) +f_s (2.14 kHz @Synch. Osc.)

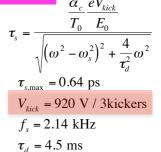






Residual Kicks to electron bunches in the adjacent RF buckets $\rightarrow 1/10 \sim 1/20$





Input Power per each kicker cell

 $P_w = 2*(V_{peak}^2/50/2) \sim 44 \text{ (W/kicker)}$

Shunt Impedance per one cell

 $R_s = (V_{kick}/3)^2 / P_w/2 = (920/3)^2 / 44/2 = 1.1 \text{ (k}\Omega)$

Shunt impedance per unit length is three times larger than that of waveguide overloaded cavity (WOC) type kicker.